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IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A structure of a light emitting diode (LED), comprising:
 - a substrate;
 - a bragg reflector layer located on said substrate, wherein said bragg reflector comprises:
 - a plurality of oxidizable semiconductor layers, wherein each of said plurality of oxidizable semiconductor layers is oxidized to form a current insulating layer; and
 - a plurality of hardly oxidized semiconductor layers, wherein said plurality of oxidizable semiconductor layers and said plurality of hardly oxidized semiconductor layers are alternately stacked on each other, wherein said plurality of oxidizable semiconductor layers are easier to oxidize than said plurality of hardly oxidized semiconductor layers ;
 - an LED epitaxial structure located on said bragg reflector layer, wherein said LED epitaxial structure comprises an n-type III-V compound semiconductor layer, an illuminating active layer, and a p-type III-V compound semiconductor layer;
 - a first electrode located on an exposed portion of said n-type III-V compound semiconductor layer; and
 - a second electrode located on an exposed portion of said p-type III-V compound semiconductor layer.
2. (Cancelled)
3. (Currently Amended) The structure according to claim 1, wherein said plurality of hardly oxidized semiconductor layers in said bragg reflector layer are AlGaInP layers.

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4. (Currently Amended) The structure according to claim 1, wherein said plurality of hardly oxidized semiconductor layers in said bragg reflector layer are AlInP layers.

5. (Currently Amended) The structure according to claim 1, wherein said plurality of hardly oxidized semiconductor layers in said bragg reflector layer are low aluminum-contained AlGaAs layers.

6. (Currently Amended) The structure according to claim 1, wherein said plurality of oxidizable semiconductor layers in said bragg reflector layer are high aluminum-contained AlGaAs layers.

7. (Currently Amended) The structure according to claim 1, wherein the aluminiferous content of said high aluminum-contained AlGaAs layers are between about 80% and about 100%.

8. (Currently Amended) The structure according to claim 6, wherein said current insulating layer is formed by oxidizing each of said high aluminum-contained AlGaAs layers at a temperature between about 300 and about 800 degree C.

17. (New) A structure of a light emitting diode (LED), comprising:
a substrate;
a bragg reflector layer located on said substrate, wherein said bragg reflector comprises:

a plurality of oxidizable semiconductor layers, wherein each of said plurality of oxidizable semiconductor layers is oxidized to form a current insulating layer, and said plurality of oxidizable semiconductor layers are high aluminum-contained AlGaAs layers, wherein the aluminiferous content of said high aluminum-contained AlGaAs layers are between about 80% and about 100%; and

a plurality of hardly oxidized semiconductor layers, wherein said plurality of oxidizable semiconductor layers and said plurality of hardly oxidized semiconductor

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layers are alternately stacked on each other, wherein said plurality of oxidizable semiconductor layers are low aluminum-contained AlGaAs layers ;
an LED epitaxial structure located on said bragg reflector layer, wherein said LED epitaxial structure comprises an n-type III-V compound semiconductor layer, an illuminating active layer, and a p-type III-V compound semiconductor layer;
a first electrode located on an exposed portion of said n-type III-V compound semiconductor layer; and
a second electrode located on an exposed portion of said p-type III-V compound semiconductor layer.